Location: GER 38

O 99: Electronic Structure Theory: New Concepts and Developments in Density Functional Theory and Beyond - VII

Time: Thursday 16:00-18:30

Invited Talk O 99.1 Thu 16:00 GER 38 Spectacular success of DFT in predicting novel topological phases — •Arun Bansil — Northeastern Univ, Boston USA

The revolutionary discovery of topological insulators has turned out to be the proverbial tip of the much larger iceberg of exotic phases of quantum matter driven by spin-orbit coupling effects. The consideration of electronic states protected by time-reversal, crystalline and particle-hole symmetries has led to the prediction of many novel materials that can support Weyl, Dirac and Majorana fermions, and to new types of topological crystalline and Kondo insulators, and quantum spin Hall insulators with large band gaps. The first-principles DFTbased band theory paradigm has been a key player not only in this discovery process but also in identifying salient characteristics of topological states, enabling direct and sharpened confrontation between theory and experiment. [1] I will discuss our recent theoretical work aimed at predicting topological materials and identify cases where the materials have been realized successfully. [2-10] I will also comment on the potential of topological materials as next generation platforms for manipulating spin and charge transport and other applications.

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Chang et al, Sci. Adv. 2, e1600295 (2016).
Huang et al., PNAS 113, 1180 (2016).
Zheng et al., ACS Nano 10, 1378 (2016).
Xu et al., Science 349, 613 (2015).
Zeljkovic et al., Nat. Mat. 14, 318 (2015).
He et al., Nat. Mat. 14, 577 (2015).
Xu et al., 748 (2015).
Crisostomo et al., Nano Lett. 15, 6568 (2015).
Xu et al., Sci. Adv. 1, e1501092 (2015).

O 99.2 Thu 16:30 GER 38

Interlayer excitons and Band Alignment in $MoS_2/hBN/WSe_2$ van der Waals Heterostructures — •SIMONE LATINI — Technical University of Denmark, Copenhagen, Denmark

Van der Waals Heterostructures (vdWHs) are a unique platform for the realization of novel (opto)-electronic devices with embedded multifunctionality. Combining two-dimensional (2D) semiconductors with misaligned band edges can lead to the formation of photo-excited electrons and holes localized in distinct layers, which result into interlayer excitons. Understanding the energetics behind the formation of interlayer excitons is the first step towards the engineering of charge separation processes in photovoltaic devices and photodetectors. The contribution of our work is then twofold. (I) We calculate, for the first time, the interlayer exciton binding energies in complex vdWHs, specifically MoS₂/hBN/WSe₂ heterostructures, using a first-principles approach. The binding energy is of extreme technological importance as it is a measure of how strongly the electron-hole pair is bound and hence how easily it can be separated. (II) We obtain accurate electronic band edges at the interface between the layers of the vdWHs, a task which could not yet be accomplished with any available state of the art technique. Importantly, the accuracy of our calculated exciton binding energies and band edges is confirmed by a striking agreement with experimental data on photoluminesce of interlayer excitons in $MoS_2/hBN/WSe_2$ heterostructures.

O 99.3 Thu 16:45 GER 38

Trionic effects in graphene nanoribbons and further nanomaterials — •THORSTEN DEILMANN and KRISTIAN SOMMER THYGESEN — Center for Atomic-Scale Materials Design (CAMD), Department of Physics, Technical University of Denmark, DK-2800 Kongens Lyngby, Denmark

Among low-dimensional materials armchair-edged graphene nanoribbons are very promising candidates with optical properties which are dominates by excitons. In the presence of additional charges, trions (i.e. charged excitons) can occur in the optical spectrum. With our recently developed first-principle many-body approach [1], we predict strongly bound trions in nanoribbons with decreasing binding energies of 660 to 140 meV for widths of 3.6 to 14.6 Å. We determine their optical spectra and identify several trions by their real-space wave functions. [1] Phys. Rev. Lett. **116**, 196084.

O 99.4 Thu 17:00 GER 38 Interface Structure Prediction using the Ab Initio Random Structure Searching Method — •GEORG SCHUSTERITSCH and CHRIS PICKARD — Department of Materials Science and Metallurgy, University of Cambridge, 27 Charles Babbage Road, Cambridge CB3 0FS, U.K.

First-principles structure prediction of bulk materials is now routinely performed, however the field of predicting the atomic structure of interfaces is still in its infancy. A detailed understanding of and ability to predict the atomic structure of interfaces is however of crucial importance for many technologies. Interfaces are very hard to predict due to the complicated geometries, crystal orientations and possible non-stoichiometric conditions involved and provide a major challenge to structure prediction. We present here the ab initio random structure searching (AIRSS) method and how it can be used to predict the structure of interfaces. Our method relies on generating random structures in the vicinity of the interface and relaxing them within the framework of density functional theory. The method is simple, requiring only a small set of parameters, and can be efficiently run on modern parallel computer architectures. We focus here on the prediction of grain boundaries, but application to heterostructure interfaces is straightforward. Examples for several grain boundary defects in technologically important materials will be presented: In particular grain boundaries in graphene, the prototypical two-dimensional material will be discussed, alongside with examples of grain boundaries in transition metal oxides, such as SrTiO3 and TiO2.

O 99.5 Thu 17:15 GER 38 **Predicting new materials and their properties with super computers: the example of perovskites** — •SILVANA BOTTI¹ and MIGUEL A.L. MARQUES² — ¹Institut für Festkörpertheorie und -optik, Friedrich-Schiller Universität Jena, Max-Wien-Platz 1, 07743 Jena — ²Institut für Physik, Martin-Luther-Universität Halle-Wittenberg, D-06099 Halle, Germany

Can new materials with optimized properties be designed using supercomputers?

I will try to convince you through the example of the search of new perovskites that first-principles calculations can efficiently speed up the discovery of new materials.

Theoretical approaches based and going beyond density functional theory ally today accuracy and efficiency, and are therefore suitable tools for understanding the physics not only of simple perfect crystals, but also of nanostructured materials, doped semiconductors, interfaces, alloys, etc. As a result, ab initio simulations of spectroscopic properties can finally account for the complexity of "real" experimental samples, allowing accurate comparison of calculated and measured structural and excitation properties. The powerful combination of theoretical spectroscopy with high-throughput calculations, structural prediction and machine learning can therefore provide a precious guide to experimentalists in the search of new materials.

O 99.6 Thu 17:30 GER 38

Spectral property prediction with artificial neural networks – •ANNIKA STUKE¹, MILICA TODOROVIC¹, KUNAL GHOSH², AKI VEHTARI², and PATRICK RINKE¹ – ¹Department of Applied Physics, Aalto University, Finland – ²Helsinki Institute of Information Technology, Department of Computer Science, Aalto University, Finland

The ability to efficiently design new and advanced optoelectronic materials is hampered by the lack of suitable methods to rapidly and accurately identify yet-to-be-synthesized materials that meet a desired application. To overcome such design challenges, a machine learning model based on a deep multi-task artificial neural network (ANN) is presented that can predict spectral properties of small organic molecules. The ANN is trained and validated on data generated by accurate state-of-the art quantum chemistry computations for diverse subsets of the GDB-13 and GDB-17 datasets [1,2]. The molecules are represented by a simple, easily attainable numerical description based on nuclear charges and cartesian coordinates and are mapped onto multiple excited-state properties simultaneously using a deep ANN trained by gradient descent and error backpropagation [3]. This on-demand prediction model can be used to infer spectral properties of various candidate molecules in an early screening stage for new optoelectronic materials at negligible computational cost, thereby completely bypassing conventional laborious approaches towards materials discovery.

[1] L. C. Blum et al., J. Am. Chem. Soc. 2009, 131, 8732, [2] R. Ramakrishnan et al., Scientific Data 2014, 1, 140022, [3] G. Montavon et al., New J. Phys. 2013, 15, 095003

O 99.7 Thu 17:45 GER 38 Machine-Learning Based Interatomic Potential for Amorphous Carbon — •VOLKER DERINGER and GÁBOR CSÁNYI — University of Cambridge, Cambridge, UK

Machine-learning based interatomic potentials are currently of growing interest in the solid-state theory communities, as they enable materials simulations with close-to DFT accuracy but at much lower computational cost. Here, we present such an interatomic Gaussian approximation potential (GAP) model for liquid and amorphous carbon. We first discuss the maximum accuracy that any finite-range potential can achieve in carbon structures; then, we show how a hierarchical set of two-, three-, and many-body structural descriptors can be used to fit a GAP that indeed reaches the target accuracy. The new potential yields accurate energetic and structural properties over a wide range of densities; it also correctly captures the structure of the liquid phases, at variance with state-of-the-art empirical potentials. Exemplary applications to surfaces of "diamond-like" tetrahedral amorphous carbon (ta-C) will be presented, including simulations of high-temperature surface reconstructions ("graphitization"). The method appears to be promising for realistic and accurate simulations of nanoscale amorphous carbon structures.

O 99.8 Thu 18:00 GER 38

High-throughput computational search for new high mobility transparent (semi)conducting materials — •GEOFFROY HAUTIER¹, JOEL VARLEY², ANNA MIGLIO¹, DAVID WAROQUIERS¹, VIET-ANH HA¹, and GIAN-MARCO RIGNANESE¹ — ¹Université catholique de Louvain, Louvain-la-Neuve, Belgium — ²Lawrence Livermore National Laboratory

Transparent conducting oxides (TCMs) are large band gap materials (to favor transparency) doped with electrons (n-type) or holes (p-type). TCMs are essential to many technologies from solar cell to transparent electronics and there is currently a large effort towards the discovery of new TCMs. I will present the results of a high-throughput computational search for new TCMs especially directed at p-type materials. Focusing on low effective masses (leading to high mobility), large band gaps and dopability, I will show how thousands of compounds can be screened using various ab initio techniques (from density functional theory to GW) to find new potential high performance TCMs. I will discuss several unsuspected compounds with promising electronic structures and when available link our findings to experimental results. Beyond the description of those novel TCM candidates, I will chemically rationalize our findings, highlighting several design strategies towards the development of future high mobility TCMs.

O 99.9 Thu 18:15 GER 38 Cross-validation in the cluster expansion method — •Axel Hübner, Santiago Rigamonti, and Claudia Draxl — Humboldt-Universität zu Berlin

The cluster expansion technique allows the construction of model Hamiltonians for an efficient evaluation of the total energy of alloys. This technique relies on a fit to a small set of *ab-initio* calculations for selected atomic configurations. Key aspects to maximize the predictive performance of the model are the selection of a set of basis functions, i.e. clusters, and of configurations. To achieve this, the cross-validation technique is typically used [1]. In this work, an analytical formula for the calculation of the leave-many-out cross-validation score (CV) is derived. This formula exhibits numerical instabilities, whose analytical properties yield a criterion for structure selection in cluster expansions. Moreover, a relation between the noise in the data and the CV is outlined. This leads to a tool which allows us to estimate, for a given noise level, the size of the ab-initio data set upon which no improvements of the model are obtained. These results are exemplified for a cluster expansion of the thermoelectric clathrate alloy $Ba_8Al_xSi_{46-x}$, calculated with the CELL package [2].

[1] A. van d. Walle $et\ al.,$ Journal of Phase Equilibria 23 (2002), Aug., Nr. 4

[2] M. Troppenz *et al.*, submitted (2016); S. Rigamonti *et al.*, in preparation.